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Kind regards,

Team Nexperia

DATA SHEET

PEMH7; PUMH7
NPN/NPN resistor-equipped
transistors; R1 = 4.7 k Ω , R2 = open

Product data sheet
Supersedes data of 2001 Oct 22

2003 Oct 02

**NPN/NPN resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = open**

PEMH7; PUMH7

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	50	V
I _O	output current (DC)	–	100	mA
TR1	NPN	–	–	–
TR2	NPN	–	–	–
R1	bias resistor	4.7	–	kΩ
R2	bias resistor	open	–	–

DESCRIPTION

NPN/NPN resistor-equipped transistors (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE ⁽¹⁾	NPN/PNP COMPLEMENT	PNP/PNP COMPLEMENT
	PHILIPS	EIAJ			
PEMH7	SOT666	–	H3	PEMD6	PEMB3
PUMH7	SOT363	SC-88	H*7	PUMD6	PUMB3

Note

1. * = p: Made in Hong Kong.
* = t: Made in Malaysia.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PEMH7 PUMH7	<p>Top view MAM453</p>	1	emitter TR1
		2	base TR1
		3	collector TR2
		4	emitter TR2
		5	base TR2
		6	collector TR1

NPN/NPN resistor-equipped transistors;
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PEMH7; PUMH7

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PEMH7	–	Plastic surface mounted package; 6 leads	SOT666
PUMH7	–	Plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _O	output current (DC)		–	100	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	–	200	mW
	SOT666	notes 1 and 2	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	–	300	mW
	SOT666	notes 1 and 2	–	300	mW

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

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PEMH7; PUMH7

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transistor				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	–	–	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	–	–	1	μ A
		V _{CE} = 30 V; I _B = 0; T _J = 150 °C	–	–	50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	–	–	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	200	330	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA	–	–	100	mV
R1	input resistor		3.3	4.7	6.1	k Ω
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0; f = 1 MHz	–	–	2.5	pF

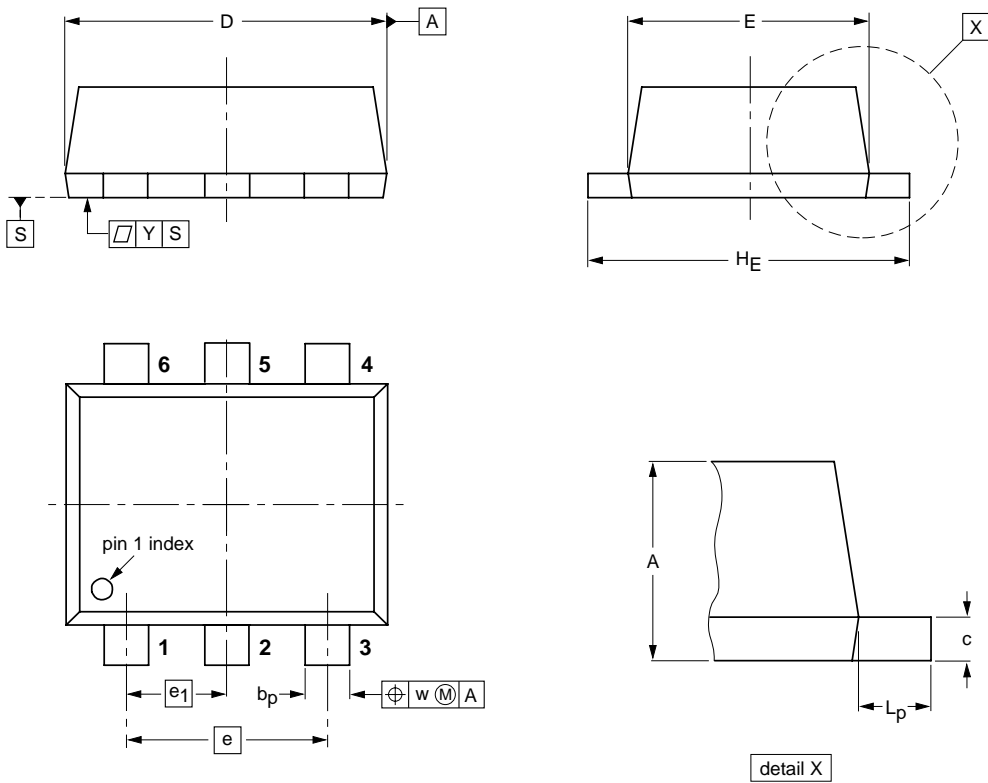
NPN/NPN resistor-equipped transistors;
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PEMH7; PUMH7

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

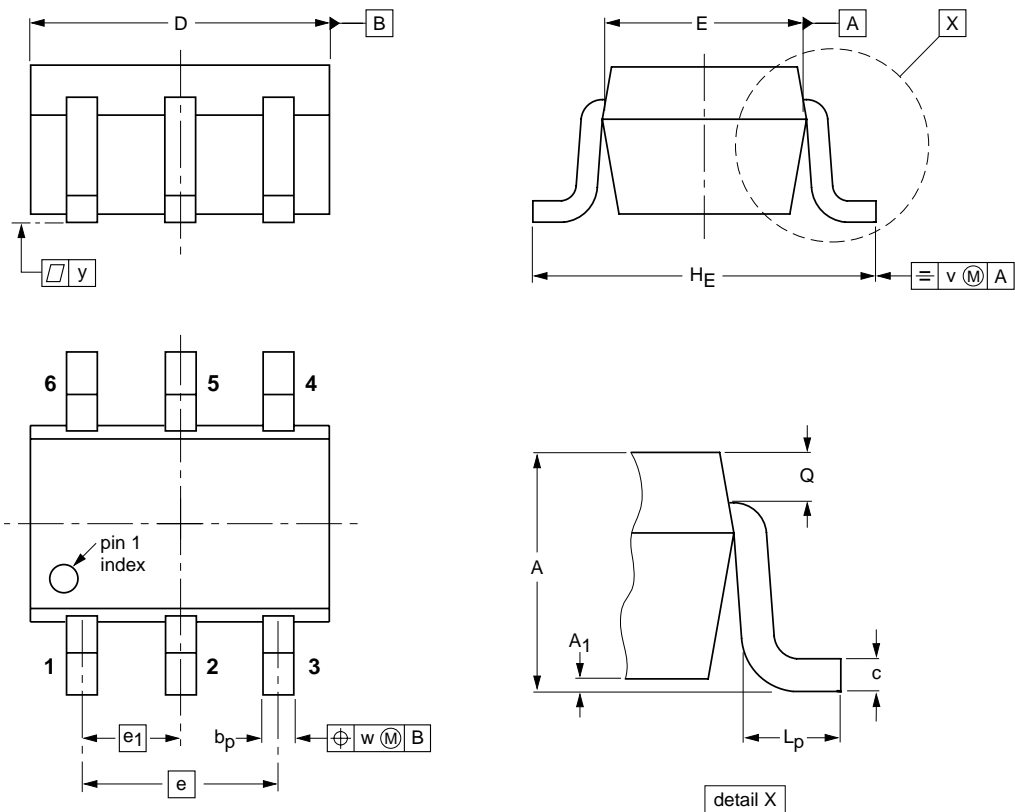
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						01-01-04 01-08-27

NPN/NPN resistor-equipped transistors;
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PEMH7; PUMH7

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

NPN/NPN resistor-equipped transistors;
 R1 = 4.7 kΩ, R2 = open

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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